

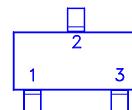
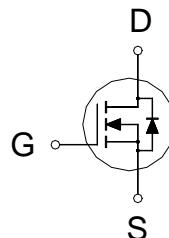
NIKO-SEM**N-Channel Logic Level Enhancement Mode
Field Effect Transistor****P8503BMG**

SOT-23

Halogen-Free & Lead-Free

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	85m Ω	2.4A



1. GATE
2. DRAIN
3. SOURCE

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS		UNITS
Gate-Source Voltage		V_{GS}	± 20		V
Continuous Drain Current	$T_A = 25^\circ\text{C}$	I_D	2.4		A
	$T_A = 100^\circ\text{C}$		1.5		
Pulsed Drain Current ¹		I_{DM}	10		
Avalanche Current		I_{AS}	12		A
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	7		mJ
Power Dissipation	$T_A = 25^\circ\text{C}$	P_D	0.75		W
	$T_A = 100^\circ\text{C}$		0.3		
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150		$^\circ\text{C}$
Lead Temperature (1/16" from case for 10 sec.)		T_L	275		

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	$R_{\theta JA}$		166	$^\circ\text{C} / \text{W}$

¹Pulse width limited by maximum junction temperature.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	30			V
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	0.8	1.7	2.5	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24\text{V}, V_{GS} = 0\text{V}$			1	μA
		$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}, T_J = 125^\circ\text{C}$			10	

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On-State Drain Current ¹	I _{D(ON)}	V _{DS} = 10V, V _{GS} = 10V	10			A
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 4.5V, I _D = 1.5A		72	115	mΩ
		V _{GS} = 10V, I _D = 3A		50	85	
Forward Transconductance ¹	g _{fs}	V _{DS} = 15V, I _D = 3A		16		S

DYNAMIC

Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 15V, f = 1MHz		217		pF	
Output Capacitance	C _{oss}			68			
Reverse Transfer Capacitance	C _{rss}			46			
				3			
Total Gate Charge ²	Q _{g(4.5V)}	V _{DS} = 0.5V _{(BR)DSS} , I _D = 3A		6.2		nC	
	Q _{g(10V)}			0.7			
Gate-Source Charge ²	Q _{gs(4.5V)}			0.7		nC	
	Q _{gs(10V)}			1.5			
Gate-Drain Charge ²	Q _{gd(4.5V)}	V _{DS} = 15V, R _L = 1Ω I _D ≈ 3A, V _{GS} = 10V, R _{GS} = 2.5Ω		2.1		nS	
	Q _{gd(10V)}			6.0			
Turn-On Delay Time ²	t _{d(on)}			6.0		nS	
Rise Time ²	t _r			6.0			
Turn-Off Delay Time ²	t _{d(off)}			20			
Fall Time ²	t _f			5.0			

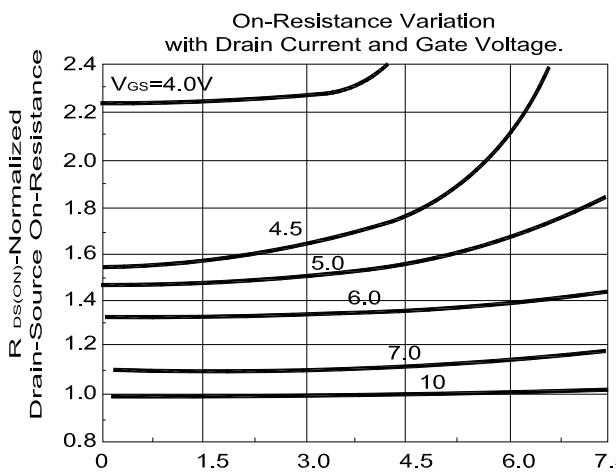
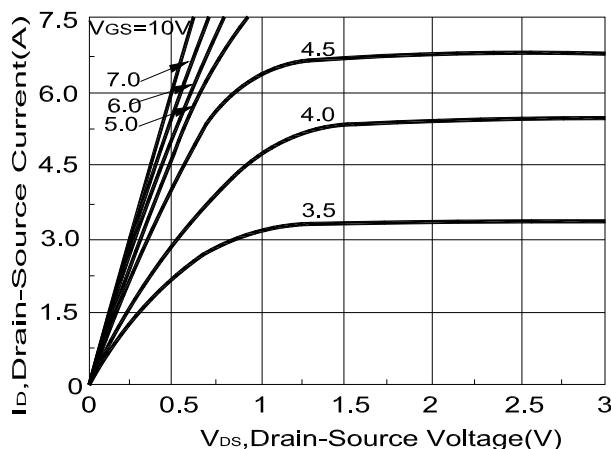
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_A = 25 °C)

Continuous Current	I _S				2.3	A
Forward Voltage ¹	V _{SD}	I _F = I _S , V _{GS} = 0V			1.5	V

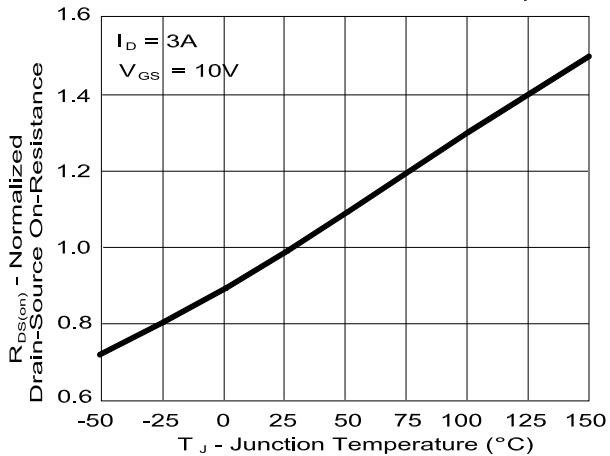
¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.²Independent of operating temperature.**REMARK: THE PRODUCT MARKED WITH “1JYWW”, DATE CODE or LOT #**

Typical Electrical Characteristics

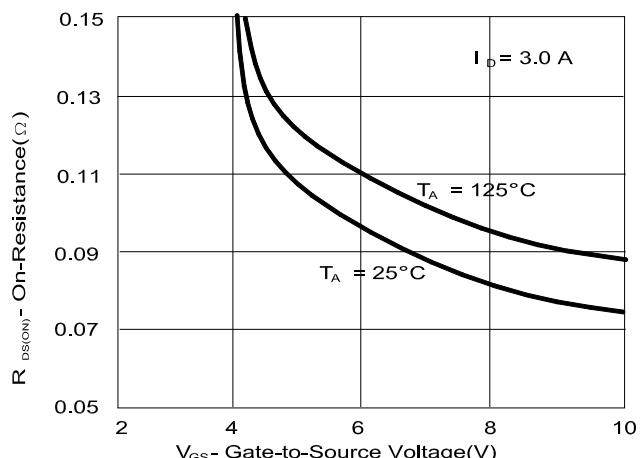
On-Region Characteristics.



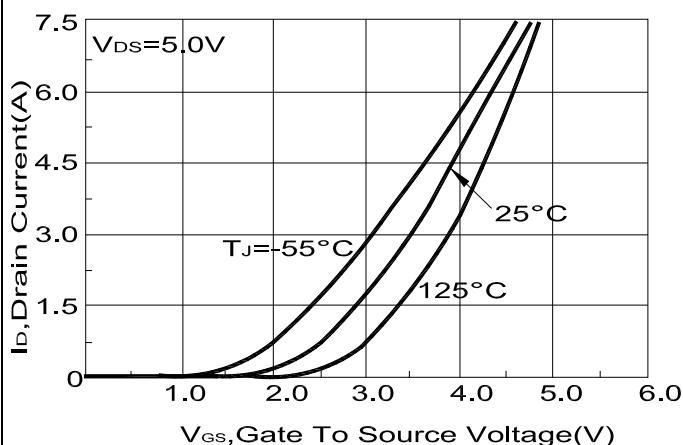
On-Resistance Variation with Temperature



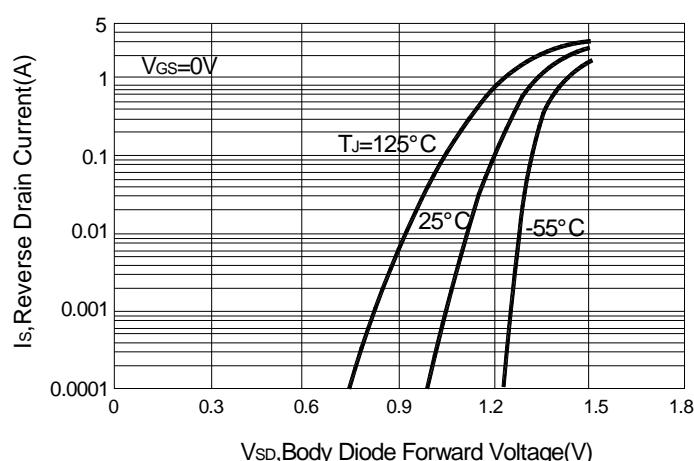
On-Resistance Variation with Gate-to-Source Voltage



Transfer Characteristics.



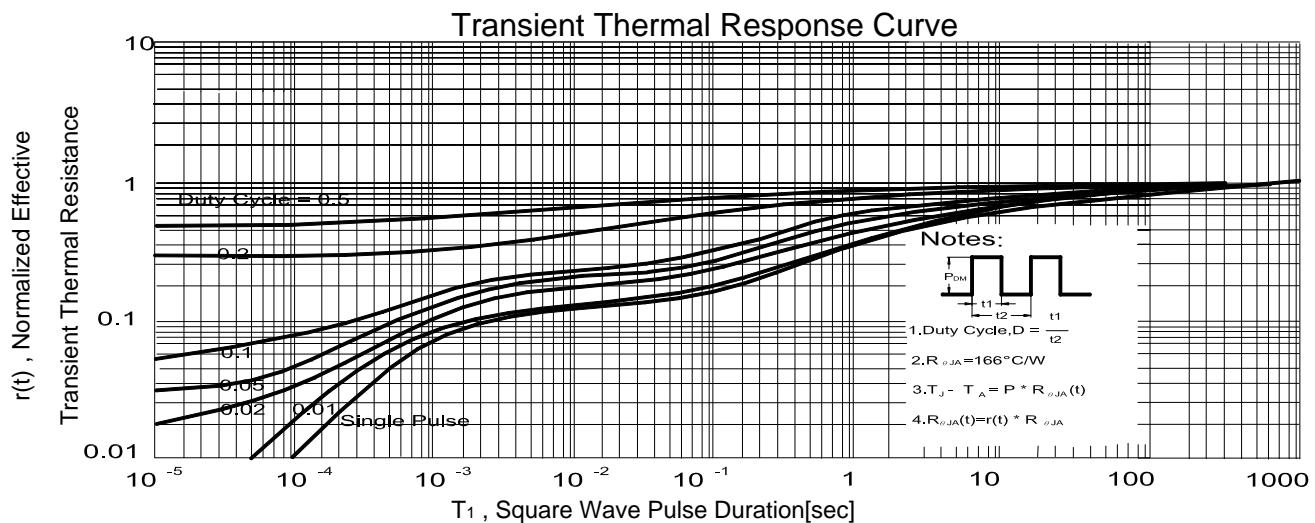
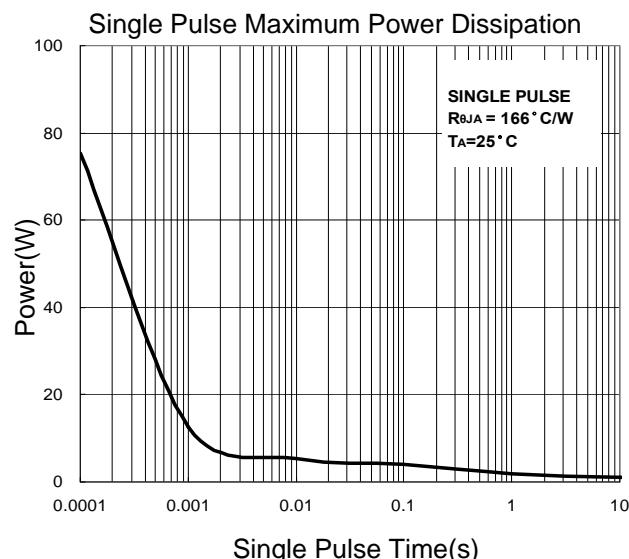
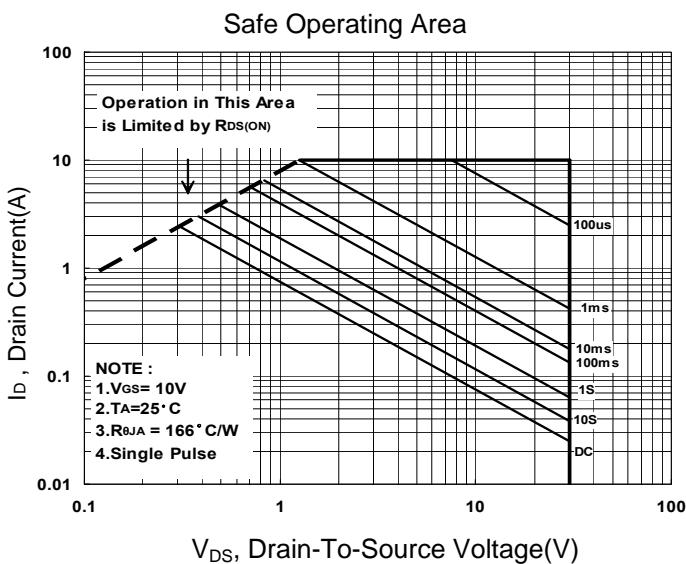
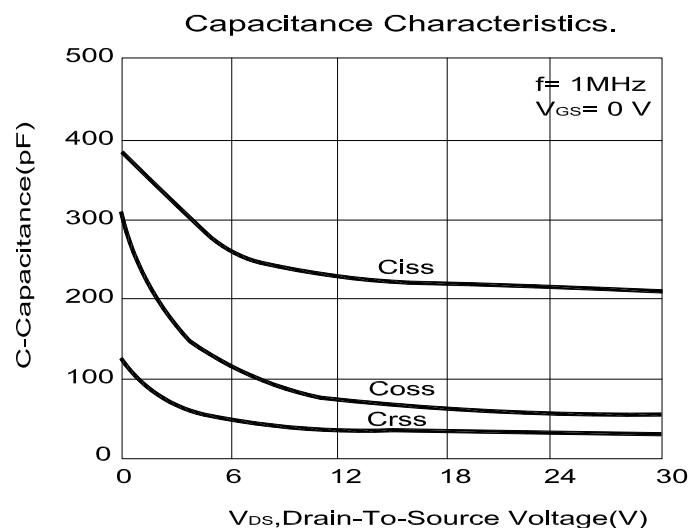
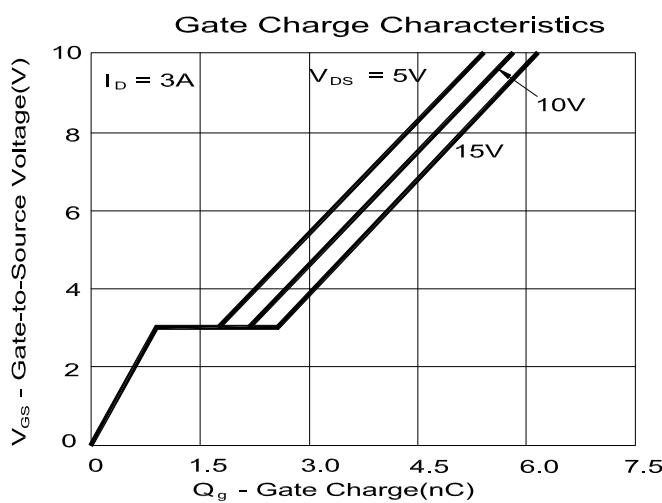
Body Diode Forward Voltage Variation with Source Current and Temperature.



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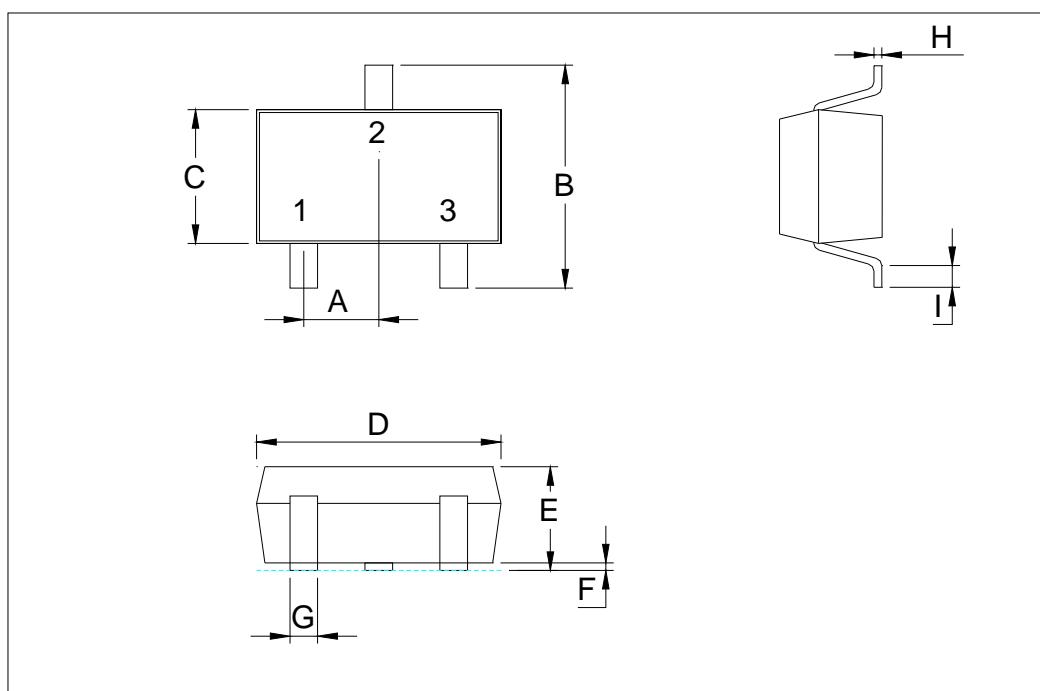
SOT-23

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SOT-23 (M3) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	0.85	0.95	1.15	H	0.1	0.15	0.35
B	2.4		3	I	0.2		0.6
C	1.4	1.6	1.8	J			
D	2.7	2.9	3.1	K			
E	0.9	1.1	1.4	L			
F	0		0.1	M			
G	0.3	0.4	0.5	N			



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